Central™
Semiconductor Corp.

PROCESS CP394R

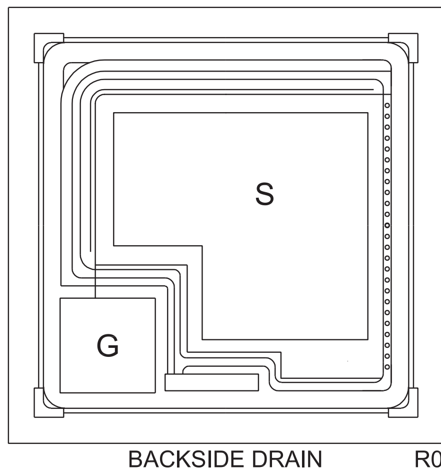
Small Signal MOSFET Transistor

N-Channel Enhancement-Mode Transistor Chip

PROCESS DETAILS

Die Size	15.7 x 15.7 MILS
Die Thickness	3.9 MILS
Gate Bonding Pad Area	3.9 x 3.9 MILS
Source Bonding Pad Area	9.1 x 8.1 MILS
Top Side Metalization	Al-Si - 35,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE DRAIN R0

GROSS DIE PER 6 INCH WAFER
95,200

PRINCIPAL DEVICE TYPES
CEDM7004

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

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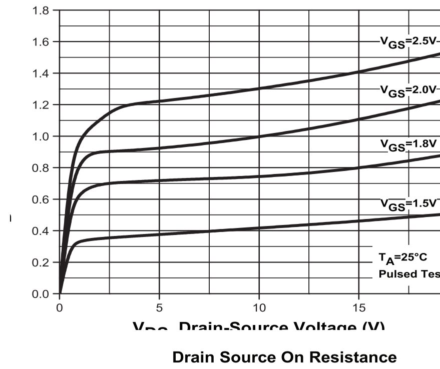
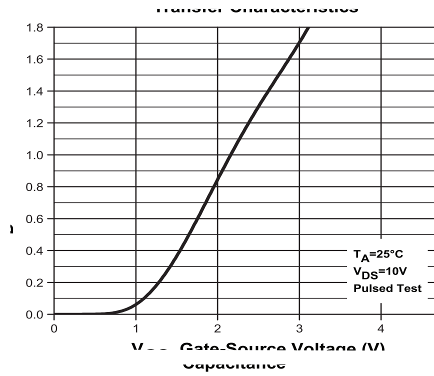
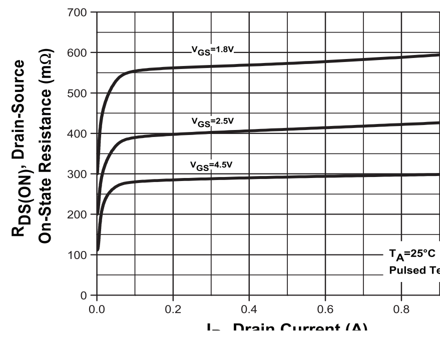
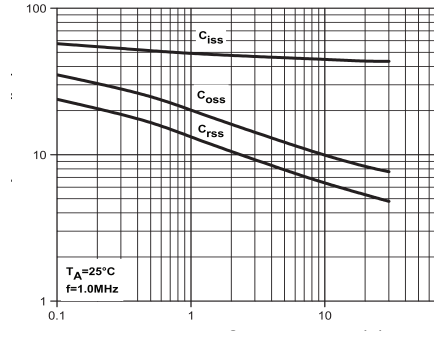
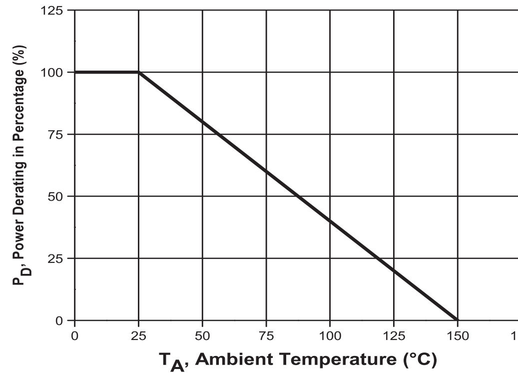
PROCESS CP394R
Typical Electrical Characteristics











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